

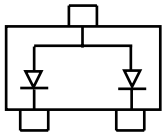
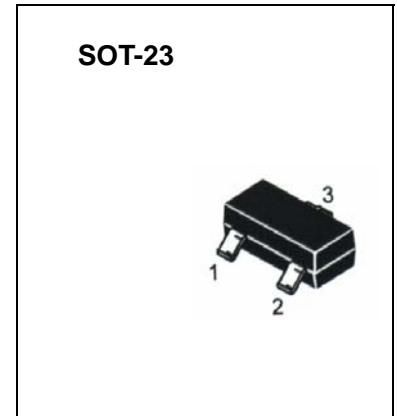


## SOT-23 Plastic-Encapsulate Diodes

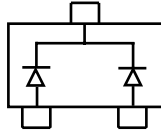
### BAW56/BAV70/BAV99 SWITCHING DIODE

#### FEATURES

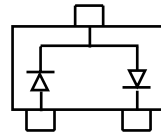
- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



BAW56 Marking: A1



BAV70 Marking: A4



BAV99 Marking: A7

#### Maximum Ratings @T<sub>A</sub>=25°C

Parameter	Symbol	Limits	Unit
Reverse voltage	V <sub>R</sub>	70	V
Forward Current	I <sub>F</sub>	200	mA
Peak Forward Surge Current @t=8.3ms	I <sub>FM(surge)</sub>	2.0	A
Power Dissipation	P <sub>D</sub>	225	mW
Thermal Resistance Junction to Ambient Air	R <sub>θJA</sub>	556	°C/W
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature range	T <sub>STG</sub>	-55-150	°C

#### Electrical Characteristics @T<sub>A</sub>=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V <sub>R</sub>	70			V	I <sub>R</sub> =100μA
Forward voltage	V <sub>F1</sub>			0.715	V	I <sub>F</sub> =1mA
	V <sub>F2</sub>			0.855	V	I <sub>F</sub> =10mA
	V <sub>F3</sub>			1	V	I <sub>F</sub> =50mA
	V <sub>F4</sub>			1.25	V	I <sub>F</sub> =150mA
Reverse current	I <sub>R</sub>			2.5	μA	V <sub>R</sub> =70V
Capacitance between terminals	C <sub>T</sub>			1.5	pF	V <sub>R</sub> =0, f=1MHz
Reverse recovery time	t <sub>rr</sub>			6	ns	I <sub>F</sub> = I <sub>R</sub> = 10mA, I <sub>rr</sub> = 0.1 x I <sub>R</sub> , R <sub>L</sub> = 100Ω